







Collaborative project-

Project acronym: SNM

Project full title: "Single Nanometer Manufacturing for beyond CMOS devices"

Grant agreement no: 318804

Deliverable: 12.4 ("SNM slide presentation for publication & EC public presentation")

Name of the coordinating person: Prof. Dr. Ivo W. Rangelow, Email: ivo.rangelow@tu-ilmenau.de List of participants:

Participant		Part. short	Activity Type	Country
no.	Participant organisation name	name		
1 (Co)	Technische Universität Ilmenau	TUIL	HER	Germany
2	EV Group E. Thallner GmbH	EVG	IND; End-user	Austria
3	IMEC	IMEC	RES	Belgium
4	Mikrosistemi Ltd	μS	SME; End-User	Bulgaria
5	Universität Bayreuth	UBT	HER	Germany
6	Technische Universiteit Delft	TUD	HER	Netherlands
7	Spanish National Research Council	CSIC	RES	Spain
8	IBM Research GmbH	IBM	IND; End-user	Switzerland
9	École polytechnique fédérale de Lausanne	EPFL	HER	Switzerland
10	SwissLitho AG	SL	SME; End-User	Switzerland
11	Oxford Instruments Nanotechnology Tools Ltd	OINT	IND; End-user	UK
12	Imperial College London	IMPERIAL	HER	UK
13	The Open University	OU	HER	UK
14	Oxford Scientific Consultants Ltd	OSC	SME	UK
15	VSL Dutch Metrology Institute	VSL	IND	Netherlands
16	University of Liverpool	ULIV	HER	UK





Page 2 of 2

SNM

Work Package 12

Deliverable: D12.4 ("SNM slide presentation for publication & EC public presentation")

Lead	1	Natu	re		R		Diss	eminatio	on		PU	
beneficiary							leve	el				
number												
Estimated	0.4					I						
Person-												
months												
Person-	TUIL											
months by	0.4											
partner for	0.4											
the			<u> </u>		I				ı		l	
Deliverable												
Estimated	04/2013			Delivery Date		06/2013						
Delivery												
Date												
Description	Presentation: see attachment											
of the												
Deliverable												
Explanation	Delay in hiring coordination assistant (He started coordination work on 01.July											
of	2013).											
Differences												
between												
Estimation												
and												
Realisation												
	1											







Single Nanometer Manufacturing for beyond CMOS devices (SNM)

Large-scale integrating project (IP) Work Program:

Challenge 3: Alternative Paths to Components and Systems
ICT 2011.3.1 Very advanced nanoelectronic components: design, engineering, technology and manufacturability

Project Consortium:







































Project Consortium

Part. Number	Partner	Partner	Country
1	TUIL	TECHNISCHE UNIVERSITÄT ILMENAU	Germany
2	EVG	EV GROUP E. THALLNER GMBH	Austria
3	IMEC	INTERUNIVERSITAIR MICRO-ELECTRONICA CENTRUM VZW	Belgium
4	μS	MIRCOSYTEMS LTD	Bulgaria
5	UBT	UNIVERSITÄT BAYREUTH	Germany
6	TUD	TECHNISCHE UNIVERSITEIT DELFT	Netherlands
7	CSIC	AGENCIA ESTATAL CONSEJO SUPERIOR DE INVESTIGACIONES CIENTIFICAS	Spain
8	IBM	IBM RESEARCH GMBH	Switzerland
9	EPFL	ECOLE POLYTECHNIQUE FEDERAL LAUSANNE	Switzerland
10	SL	SWISSLITHO AG	Switzerland
11	OINT	OXFORD INSTRUMENTS NANOTECHNOLOGY TOOLS LIMITED	United Kingdom
12	Imperial	IMPERIAL COLLEGE OF SCIENCE, TECHNOLOGY AND MEDICINE	United Kingdom
13	OU	THE OPEN UNIVERSITY	United Kingdom
14	OSC	OXFORD SCIENTIFIC CONSULTANTS LTD	United Kingdom
15	VSL	VSL B.V.	Netherlands

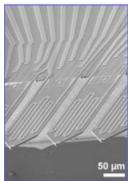


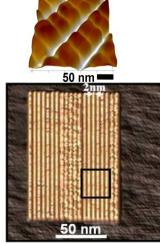
Project Targets



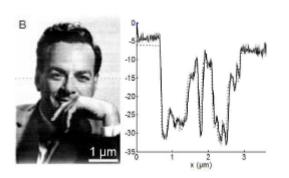


- Prototype Single Nanometer Manufacturing Technology for Industry-oriented Applications using:
- Nanoresist material and Electron Beam Induced Deposition precursors
- Integrated process flow for Fabricating Nano-Imprint
 Templates, end-of-roadmap CMOS and beyond CMOS devices
- Demonstration of Overlay Alignment Concept with ultimately Accuracy at a Nano-Imprint Lithography Production System
- Development and Investigation of Manufacturable 'beyond CMOS' Devices
- Establishment of Metrology Specifications for 'beyond CMOS' Devices









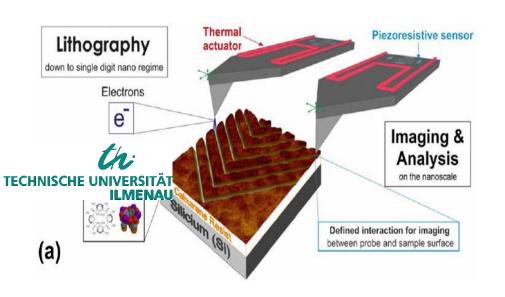




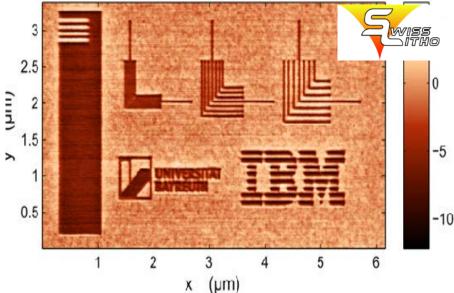


Tip-based Techniques for Single Nanometer Manufacturing

a) FN-field emission



a) Thermal tip



WPG1: Single Nanometer Lithography

Involved SNM partners: TUIL,EVG, μS,TUD,CSIC,IBM,SL,OSC





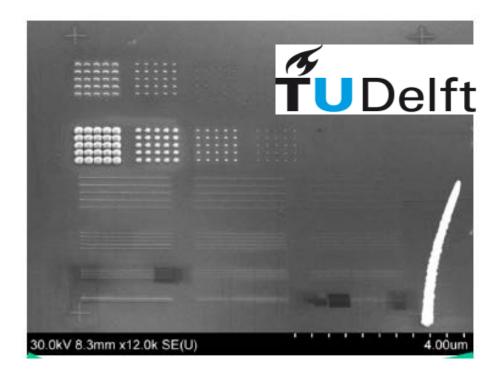


Deposition and Lithography Techniques for Single Nanometer Manufacturing

c) Tip-induced nanochemistry

d) Electron beam induced deposition lithography





WPG1: Single Nanometer Lithography

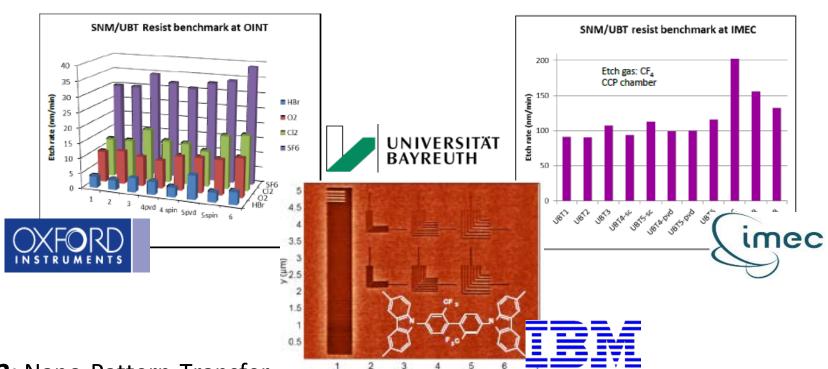
Involved SNM partners: TUIL,EVG, μS,TUD,CSIC,IBM,SL,OSC







Development and Investigation of New Resist Materials suitable for Etching and Tip-based Patterning



WPG2: Nano-Pattern-Transfer

Involved SNM partners: TUIL,IMEC,UBT,CSIC,IBM,EPFL,OINT,OSC,VSL

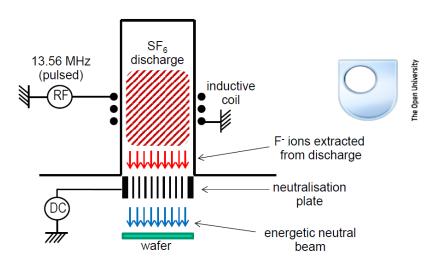




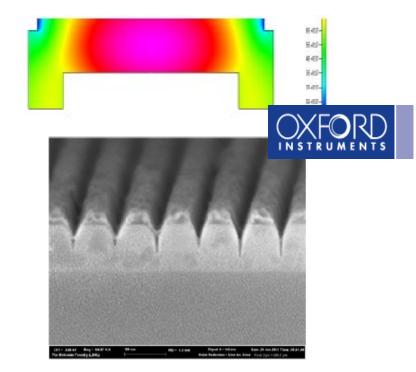


Nano-Pattern Transfer Techniques

a) Neutrals beam etching



b) Reactive ion etching (Simulation and Experiments)



WPG2: Nano-Pattern-Transfer

Involved SNM partners: TUIL,IMEC,UBT,CSIC,IBM,EPFL,OINT,OSC,VSL



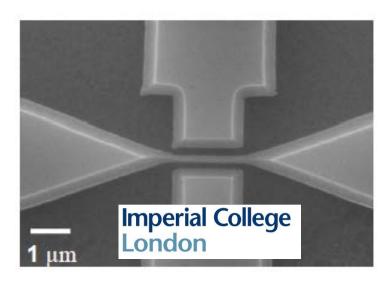


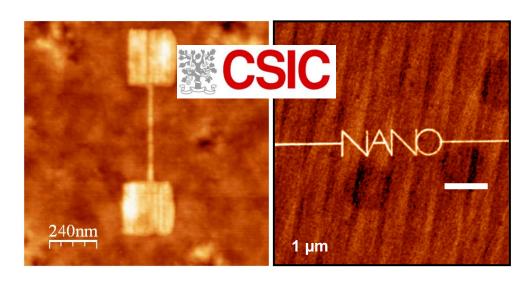


Beyond CMOS Nano-Devices based on different materials

a) Silicon NanowireSingle Electron Transistors

b) Titanium Nanowires transistors





WPG3: Beyond CMOS

Involved SNM partners: TUIL,CSIC,IBM,EPFL,Imperial

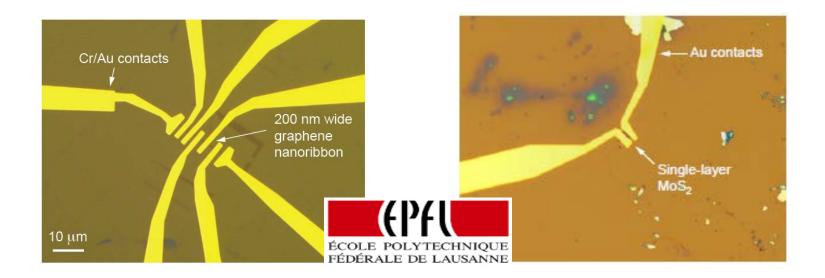






Beyond CMOS Nano-Devices based on different novel 2D materials

c) Graphene nanoribbon Field Effect Transistors d) Molybdenum Disulfid Field Effect Transistors



WPG3: Beyond CMOS

Involved SNM partners: TUIL,CSIC,IBM,EPFL,Imperial

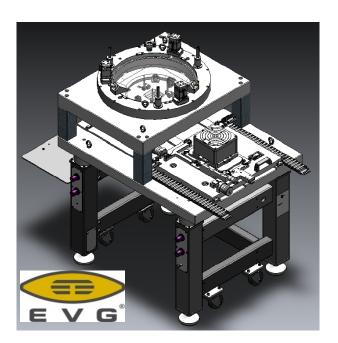




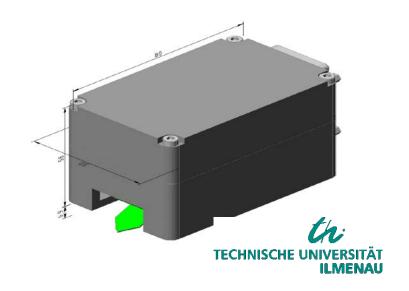


Single Nanometer Manufacturing Nano-Imprint System using Scanning Probe Microscopes for Overlay Alignment

a) Nano-Imprint System Layout



b) Specially designed and optimized "mouse-AFM"



WPG4: High-Throughput Single-Nanometer Manufacturing

Involved SNM partners: TUIL,EVG,IMEC,µS,UBT,TUD,CSIC,IBM,SL,OINT,Imperial,VSL

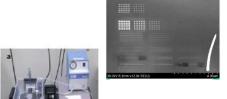


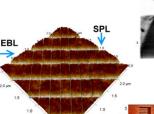


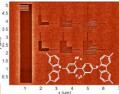


Important Achievements after Six Project Months

- Single Nanometer Structures fabricated with EBIDL
- Parallel Oxidation Lithography Device Prototype
- Complex 3D Pattern with 1nm vertical Accuracy
- Mix and Match Lithography for high Throughput combining EBL and SPL
- High Plasma Durability Molecular Glass Resists for tipbased Patterning and Pattern Transfer
- First preliminary "beyond CMOS" Devices realized
- Basic Concept of Scanning Probe Alignment Step-and-Repeat System.















Dissemination

- "International Society for Optics and Photonics" SPIE Newsroom: Scanning probe lithography for electronics at the 5nm scale, Z. Durrani, M. Kaestner, M. Hofer, Tzv. Ivanov and I.W. Rangelow
- Mix & Match Electron Beam and Scanning Probe Lithography for sub-5 nm Pattering, M. Kaestner, M. Hofer and I.W. Rangelow, The 57th International Conference on Electron, Ion and Photon beam Technology & Nanofabrication Gaylord Opryland Resort Nashville, TN May 28 - May 31, 2013
- Scanning probe lithography for electronics at the 5nm scale, Z. Durrani, M. Kaestner, M. Hofer, Tzv. Ivanov and I.W. Rangelow, SPIE 2013 Advanced Lithography 24-28 February 2013
- Scanning Probe Lithography approach for beyond CMOS devices, Z. Durrani, M. Jones, M. Kaestner, M. Hofer, E. Guliyev, A. Ahmad, Tzv. Ivanov, J.-P. Zoellner and I.W. Rangelow Advanced Lithography, Proc. SPIE - Int. Soc. Opt. Eng. 2013, submitted
- **0.1-nanometer resolution positioning stage for sub-10nm scanning probe lithography,** N. Vorbringer-Doroshovets, F. Balzer, E. Manske, M. Kaestner, A. Schuh, J.-P. Zoellner, M. Hofer, E. Guliyev, A. Ahmad, Tzv. Ivanov and I.W. Rangelow, Advanced Lithography, Proc. SPIE - Int. Soc. Opt. Eng. 2013, submitted
- Mix & Match Electron Beam & Scanning Probe Lithography for high troughput sub-10nm Lithography, M. Kaestner, M. Hofer and I.W. Rangelow, Advanced Lithography, Proc. SPIE - Int. Soc. Opt. Eng. 2013, submitted
- Nanolithography by scanning probes on calixarene molecular glass resist using Mix & Match lithography, M. Kaestner, M. Hofer and I.W. Rangelow, Invited Special Section Paper, JM3 (Journal of Micro/Nanolithography, MEMS and MOEMS, h5-index: 15) submitted
- 11 Abstacts at MNE 2013 (incl. 1 invited)
- 1 Abstract at MRS 2013







We thank you for your attention!

Single Nanometer Manufacturing for beyond CMOS devices (SNM)

Large-scale integrating project (IP) Work Program:

Challenge 3: Alternative Paths to Components and Systems
ICT 2011.3.1 Very advanced nanoelectronic components: design, engineering, technology and manufacturability

Project Consortium:



















Imperial College London











